



General Purpose Transistors

BC817-16LG, BC817-25LG,BC817-40LG

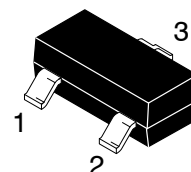
BC817-16/25/40LG SERIES

Features

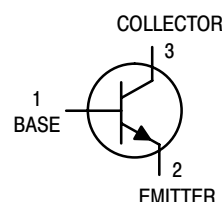
- Pb-Free Packages are Available

Maximum Ratings

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	45	V
Collector–Base Voltage	V_{CBO}	50	V
Emitter–Base Voltage	V_{EBO}	5.0	V
Collector Current – Continuous	I_C	500	mAdc



SOT-23



Device Marking

BC817–16LG = 6A; BC817–25LG = 6B; BC817–40LG = 6C

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$)	$V_{(BR)CEO}$	45	–	–	V
Collector–Emitter Breakdown Voltage ($V_{EB} = 0, I_C = -10\ \mu\text{A}$)	$V_{(BR)CES}$	50	–	–	V
Emitter–Base Breakdown Voltage ($I_E = -1.0\ \mu\text{A}$)	$V_{(BR)EBO}$	5.0	–	–	V
Collector Cutoff Current ($V_{CB} = 20\text{ V}$) ($V_{CB} = 20\text{ V}, T_A = 150^\circ\text{C}$)	I_{CBO}	– –	– –	100 5.0	nA μA

- FR–5 = 1.0 x 0.75 x 0.062 in.
- Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.

**Electrical Characteristics** ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ V}$) BC817-16LG BC817-25LG BC817-40LG ($I_C = 500\text{ mA}$, $V_{CE} = 1.0\text{ V}$)	h_{FE}	100 160 250 40	- - - -	250 400 600 -	-
Collector-Emitter Saturation Voltage ($I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$)	$V_{CE(sat)}$	-	-	0.7	V
Base-Emitter On Voltage ($I_C = 500\text{ mA}$, $V_{CE} = 1.0\text{ V}$)	$V_{BE(on)}$	-	-	1.2	V
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain - Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	-	-	MHz
Output Capacitance ($V_{CB} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	-	10	-	pF

Rating and characteristic curves

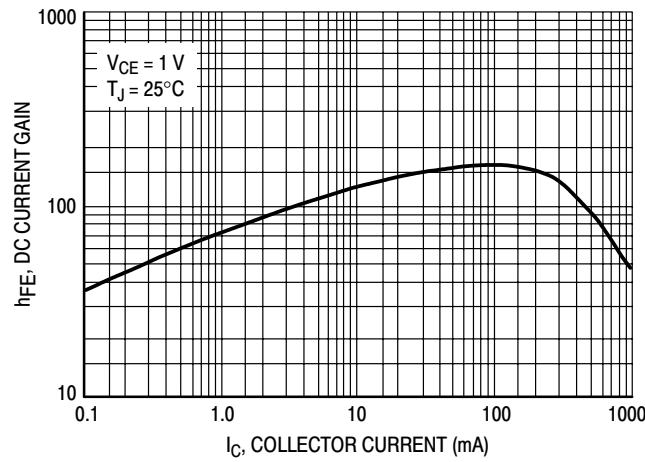


Figure 1. DC Current Gain

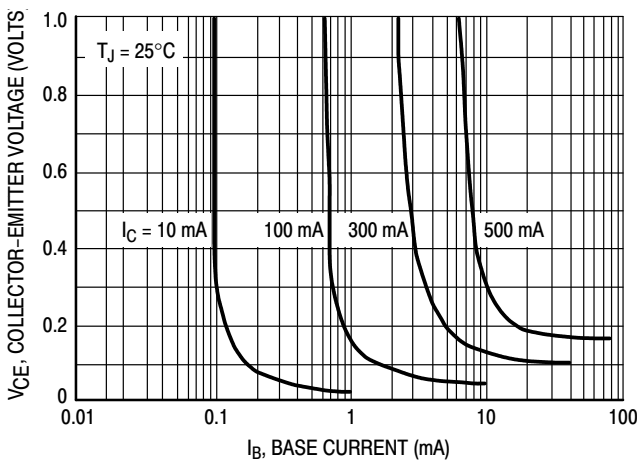


Figure 2. Saturation Region

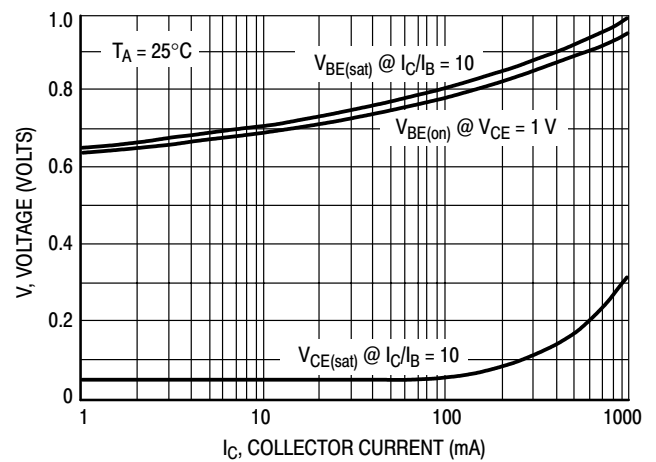


Figure 3. "On" Voltages

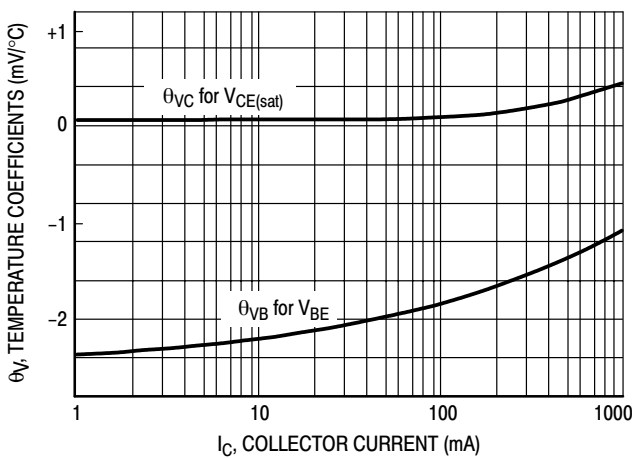


Figure 4. Temperature Coefficients

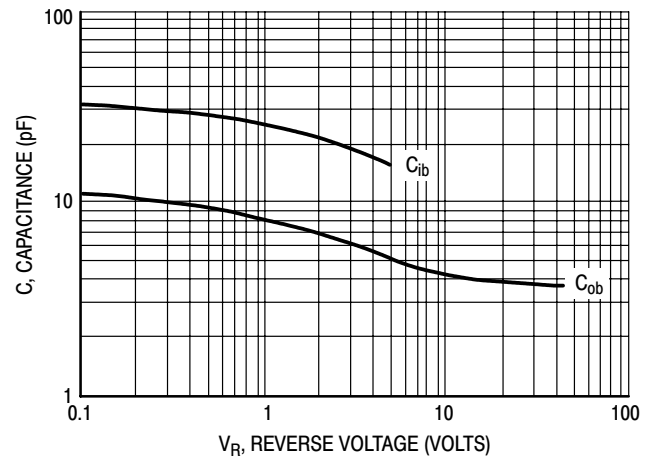
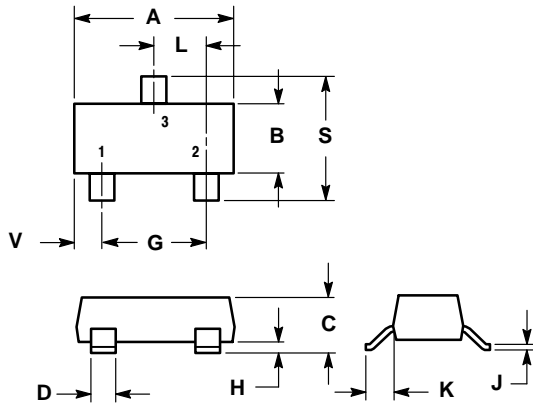


Figure 5. Capacitances

Package Dimensions

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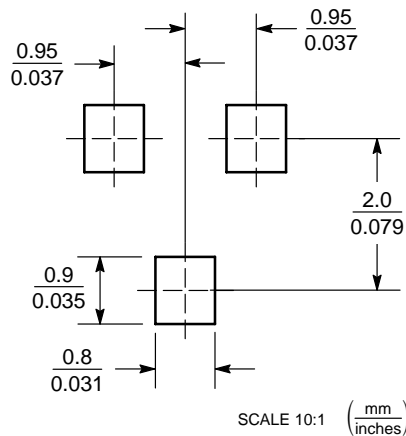


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. 318-01, -02, AND -06 OBSOLETE, NEW STANDARD 318-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0385	0.0498	0.99	1.26
D	0.0140	0.0200	0.36	0.50
G	0.0670	0.0826	1.70	2.10
H	0.0040	0.0098	0.10	0.25
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60

STYLE 6:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.